



#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	110mΩ @ V <sub>GS</sub> = -4.5V	SOT23	-2.6A
-200	225mΩ @ $V_{GS}$ = -2.5 $V$	30123	-2.0A

#### **Description**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{\text{DS(ON)}}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

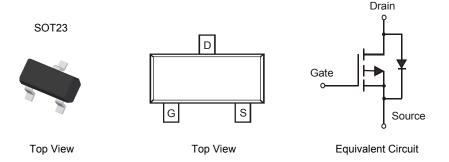
- General Purpose Interfacing Switch
- · Power Management Functions

#### **Features**

- Low On-Resistance:
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
  Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



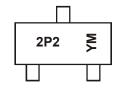
# **Ordering Information**

Part Number	Qualification	Case	Packaging
DMP2225L-7	Commercial	SOT-23	3000/Tape & Reel
DMP2225LQ-7	Automotive	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diòdes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



2P2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteris	stic		Symbol	Value	Units
Drain-Source Voltage		$V_{ t DSS}$	-20	V	
Gate-Source Voltage		$V_{GSS}$	±12	V	
Continuous Drain Current (Note 5) Stead $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	-2.6 -2	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	8	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_{D}$	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	115	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

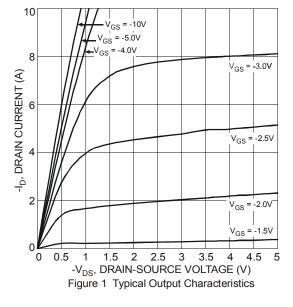
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	1 2		71-		1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-800	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
On-State Drain Current	,	-6	_	_	A	$V_{DS} \le -5V, V_{GS} = -4.5V$
On-State Drain Current	I <sub>D</sub> (ON)	-3	_	_	] ^	$V_{DS} \le -5V, V_{GS} = -2.5V$
Gate-Source Leakage	I <sub>GSS</sub>	-	_	±80	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.45	_	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance		_	80	110	mΩ	$V_{GS} = -4.5V$ , $I_D = -2.6A$
Static Diain-Source On-Resistance	R <sub>DS (ON)</sub>		165	225	11152	$V_{GS} = -2.5V$ , $I_D = -2.0A$
Forward Transfer Admittance	Y <sub>fs</sub>		4	_	S	$V_{DS} = -5V, I_{D} = -2.6A$
Diode Forward Voltage (Note 6)	$V_{SD}$	_	_	-1.26	V	$V_{GS} = 0V, I_S = -2.6A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>	l	250	_	pF	101/11/101/
Output Capacitance	Coss		88	_	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V -f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	58	_	pF	1 - 1.000112
Gate Resistance	Rg	_	12	16	Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$
Total Gate Charge	Qg		4.3	5.3		\\ - 45\\\\ - 40\\\
Gate-Source Charge	$Q_{gs}$		0.9		nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_{D} = -2.7A$
Gate-Drain Charge	$Q_{qd}$	_	2.1	_		ID2.1A

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Repetitive rating, pulse width limited by junction temperature.7. Short duration pulse test used to minimize self-heating effect.





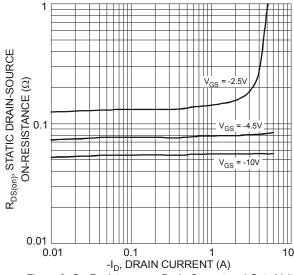


Figure 3 On-Resistance vs. Drain Current and Gate Voltage

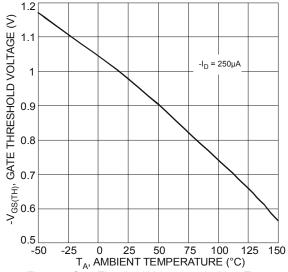
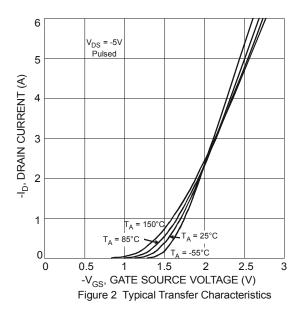
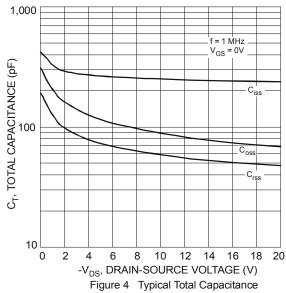


Figure 5 Gate Threshold Voltage vs. Ambient Temperature





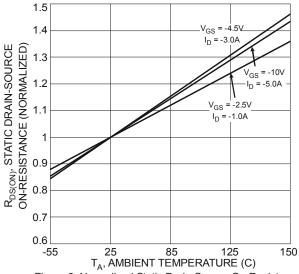


Figure 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



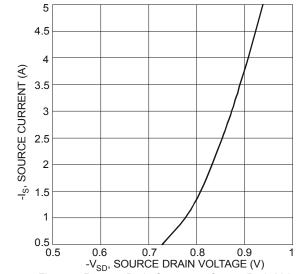
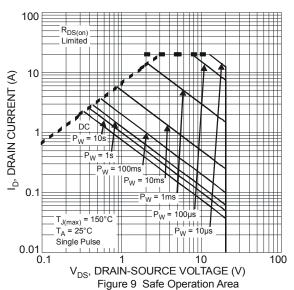
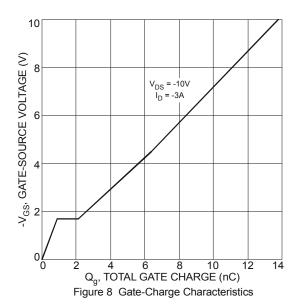
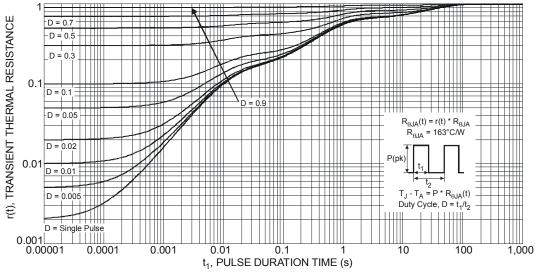


Figure 7 Reverse Drain Current vs. Source-Drain Voltage



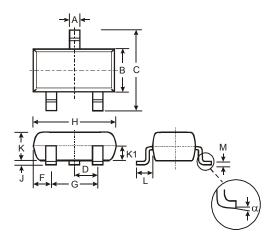






# **Package Outline Dimensions**

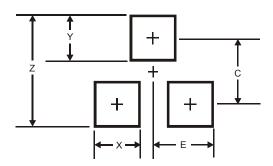
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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